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L2 "bipolar transistor"

28993 L2

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1 L1

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Bipolar Circuits and Technology Meeting, 1991., Proceedings of the 1991 , 9-1 Sept. 1991

Pages:263 - 266

[\[Abstract\]](#) [\[PDF Full-Text \(276 KB\)\]](#) **IEEE CNF**
2 Innovative localized lifetime control in high-speed IGBTs*Saggio, M.; Raineri, V.; Letor, R.; Frisina, F.;*

Electron Device Letters, IEEE , Volume: 18 , Issue: 7 , July 1997

Pages:333 - 335

[\[Abstract\]](#) [\[PDF Full-Text \(64 KB\)\]](#) **IEEE JNL**
3 Analytical modeling of oxide breakup effect on base current in n⁺-polysilicon emitter bipolar devices*Sung, J.J.; Liu, T.M.; Kim, Y.O.; Chiu, T.-Y.;*

Electron Devices, IEEE Transactions on , Volume: 39 , Issue: 12 , Dec. 1992

Pages:2797 - 2802

[\[Abstract\]](#) [\[PDF Full-Text \(508 KB\)\]](#) **IEEE JNL**
4 Hybrid power modules using a metal matrix composite baseplate: An evaluation*Azzopardi, S.; Thebaud, J.-M.; Woirgard, E.; Zardini, C.;*

IEMT/IMC Symposium, 2nd 1998 , 15-17 April 1998

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